

<b>Monday Dec. 14</b>		
<b>Room A</b>		
7:00-8:00AM	Breakfast	
<b>Session: Crystal Engineering I Chair: Cristian V. Ciobanu</b>		
8:00-8:25AM	A01: Laser-irradiation-induced crystallization of Si films: scientific opportunities and technological motivations	<b>James Im</b> Columbia University, USA
8:25-8:50AM	A02: Multi crystalline silicon solidification under controlled forced convection	<b>Kader Zaidat</b> Institut Polytechnique de Grenoble – PHELMA, France
8:50-9:15AM	A03: Thermodynamic Phase Behavior of Cocrystal Systems	<b>Gabriele Sadowski</b> TU Dortmund, Germany
9:15-9:40AM	A04: The effect of crystalline environment on molecular interactions in crystals : A further (unknown) variable in crystal engineering	<b>Enrique Espinosa</b> University of Lorraine, France
9:40-10:05AM	A05: Continuous crystallization of pharmaceuticals	<b>Richard Lakerveld</b> The Hong Kong University of Science & Technology, Hong Kong
10:05-10:20AM	Session Break	
<b>Session: Epitaxial thin films and nanostructures I Chair: Bernd Rauschenbach</b>		
10:20 -10:45AM	A06: Stability and Electrical ZnIn <sub>2</sub> O <sub>4</sub> Thin Film with Cubic Spinel Structure as a Novel Transparent Conductive Oxide	<b>Naoki Wakiya</b> Shizuoka University, Japan
10:45-11:10AM	A07: Sub-monolayer InAs/GaAs depositions without and with Sb for fast, directly driven laser devices	<b>Holger Eisele</b> Technische Universität Berlin, Germany
11:10-11:35AM	A08: Real time observation of nanowire growth and selective growth of nanocrystals	<b>Tomas Sikola</b> Brno University of Technology, Czech Republic
11:35-12:00PM	A09: Novel Dilute Bismides for IR Optoelectronics	<b>Shumin Wang</b> Chalmers University of Technology, Sweden
12:00-12:25PM	A10: Magnetic domain wall manipulation in tailored (Ga,Mn)As nanostructures for spintronic applications	<b>Tadeusz Wosinski</b> Polish Academy of Sciences, Poland
12:30-13:30PM	Lunch Break	

**Monday Dec. 14**

**Room B**

**Session: Epitaxial thin films and nanostructures II Chair: Tadeusz Wosinski**

13:30-13:55PM	B01: Sheathed Nanowires Aligned by Crystallographic Periodicity	<b>Hiroshi M. Yamamoto</b> Institute for Molecular Science, Japan
13:55-14:20PM	B02: 3D Nanostructured Materials via Atomic Layer Deposition: Fabrication & Solar Energy Harvesting / Smart Window Applications	<b>Alfred Tok</b> Nanyang Technological University, Singapore
14:20-14:45PM	B03: SiGe Sputter Epitaxy and Its Application to SiGe 2D Devices	<b>Yoshiyuki Suda</b> Tokyo University of Agriculture and Technology, Japan
14:45-15:00PM	B04: Development of MBE Air-Hole Retained Growth Technique for Fabrication of Photonic-Crystal Lasers	<b>Masaya Nishimoto</b> Kyoto University, Japan
15:00-15:15PM	B05: Synthesis of High Performance Co(Soft)/SmCo5(Hard) Nanocomposite Magnets by Core/Shell Nanoparticles for Exchange-coupled Nanocomposite	<b>Inho Kim</b> Sogang University, Korea
15:15-15:25PM	Session Break	
<b>Session: Epitaxial thin films and nanostructures III Chair: Yoshiyuki Suda</b>		
15:25-15:50PM	B06: Epitaxial GaN films prepared by hyperthermal ion beam assisted molecular beam epitaxy - an electronmicroscopical study	<b>Bernd Rauschenbach</b> IOM and University Leipzig, Germany
15:50-16:15PM	B07: Concurring kinetics of phase transition and grain growth in nanostructured alloy	<b>Feng Liu</b> Northwestern Polytechnical University, China
16:15-16:40PM	B08: Epitaxial Growth of Lead-free Piezoelectric Thin films and Superlattices	<b>Danyang Wang</b> University of New South Wales, Australia
16:40-17:05PM	B09: The unique physical properties of nanostructured diamond	<b>Changzhi Gu</b> Institute of Physics, CAS, China
17:30PM	Dinner Social	

**Monday Dec. 14**

**Room C**

**Session: 2D atomic layered materials I Chair: Toshio Ogino**

13:30-13:55PM	C01: Latent heat induced rotation limited aggregation in 2D nanocrystalline ice	<b>Bene Poelsema</b> University of Twente, The Netherlands
13:55-14:20PM	C02: Tracking Atoms, Vacancies and Electrons via Aberration-corrected Microscopy and First-Principles Theory	<b>Stephen Pennycook</b> National University of Singapore, Singapore
14:20-14:45PM	C03: Growth and functionalization of epitaxial graphene on SiC	<b>Wataru Norimatsu</b> Nagoya University, Japan
14:45-15:10PM	C04: Germanene: the germanium analogue of graphene	<b>Harold J. W. Zandvliet</b> University of Twente, The Netherlands
15:10-15:25PM	Session Break	
<b>Session: Radiation Detector Materials-From Crystal Growth to Device Applications I Chair: Daniel Bonn</b>		
15:25-15:50PM	C05: New cerium doped elpasolite single crystal scintillators for radiation detection and medical imaging applications	<b>HongJoo Kim</b> Kyungpook National University, Korea
15:50-16:15PM	C06: Development of Novel Room Temperature Semiconductor Detector (RTSD) Materials and Devices	<b>Sudhir Trivedi</b> Brimrose Technology Corporation, USA
16:15-16:40PM	C07: Crack-free growth of large diameter Strontium Iodide scintillator crystals using innovative dehydration and matrix softening techniques	<b>Amlan Datta</b> Capesym, Inc., USA
16:40-17:05PM	C08: Features of radiation-induced processes in LiF crystals containing nanoscale impurity conglomerates	<b>Liudmila Lisitsyna</b> Tomsk State University of Architecture and Building, Russia
17:30PM	Dinner Social	

**Monday Dec. 14**

**Room D**

**Session: Tunable materials Chair: Holger Eisele**

13:30-13:55PM	D01: Gold(I) Compounds with Tunable Luminescent Properties	<b>Andrea Deak</b> Hungarian Academy of Sciences, Hungary
13:55-14:20PM	D02: Controlled nucleation and growth in glass and its impact on glass bioactivity	<b>Jonathan Massera</b> Tampere University of Technology, Finland
14:20-14:45PM	D03: Thin films from topological crystalline insulators	<b>Marta Galicka</b> Polish Academy of Sciences, Poland
14:45-15:10PM	D04: Glass-ferroic composite: the third class of ferroic materials	<b>Yuanchao Ji</b> Xi'an Jiaotong University, China
15:10-15:25PM	Session Break	
<b>Session: General I Chair: Geun Woo Lee</b>		
15:25-15:50PM	D05: Importance of water in the control of inorganic crystal growth by organic molecules	<b>Hiroki Nada</b> National Institute of Advanced Industrial Science and Technology (AIST) Japan
15:50-16:15PM	D06: Synthesis of Graphene / MxWO3 Composite with Excellent Electrical Properties	<b>Shu Yin</b> Tohoku University, Japan
16:15-16:40PM	D07: Convection diffusion models accompanied with gas-phase epitaxy of semiconducting layers	<b>Pavel Boldyrevskii</b> Nizhny Novgorod Lobachevsky State University, Russia
16:40-17:05PM	D08: Fluoride crystals as potential vacuum ultraviolet laser media	<b>Nobuhiko Sarukura</b> Osaka University, Japan
17:30PM	Dinner Social	

<b>Tuesday Dec. 15</b>		
<b>Room B</b>		
7:00-8:00AM	Breakfast	
<b>Session: Epitaxial thin films and nanostructures IV Chair: Elisabeth Blanquet</b>		
8:00-8:25AM	B10: Eliminating defects in three-dimensional micro- and nanocrystals on mismatched substrates	<b>Hans Von Känel</b> ETH Zürich, Switzerland
8:25-8:50AM	B11: Growth of atomically flat diamond films	<b>Norio Tokuda</b> Kanazawa University, Japan
8:50-9:15AM	B12: Hybrid Magnetic/Semiconductor Materials : Growth, Structure and Properties	<b>Yongbing Xu</b> Nanjing University, China; The University of York, UK
9:15-9:40AM	B13: Heteroepitaxial growth of layered pnictides and chalcogenides films	<b>Hidenori Hiramatsu</b> Tokyo Institute of Technology, Japan
9:40-10:05AM	B14: Epitaxial growth of gamma-phase Ga <sub>2</sub> O <sub>3</sub> semiconductor	<b>Takayoshi Oshima</b> Tokyo Institute of Technology, Japan
10:05-10:20AM	Session Break	
<b>Session: General II Chair: Pallavi Kushwaha</b>		
10:20 -10:45AM	B15: Lattice Model Analysis Combined with LEEM Observations	<b>Noriko Akutsu</b> Osaka Electro-Communication University, Japan
10:45-11:10AM	B16: Numerical Simulation of Development of Sea Ice Microstructure with Particle Method and Voronoi Dynamics	<b>Yoshiki Kawano</b> National Institute of Technology, Japan
11:10-11:35AM	B17: Structure-function correlations in metal oxides – Insights from density functional and many body theory	<b>Eva Rauls</b> Universität Paderborn, Germany
11:35-12:00PM	B18: Bipartite bosonic modes and spin memory effects in superconducting Sr <sub>4</sub> V <sub>2</sub> O <sub>6</sub> Fe <sub>2</sub> As <sub>2</sub> investigated with variable temperature/field spin-polarized STM	<b>Jhinhwan Lee</b> KAIST, Korea
12:00-13:30PM	Lunch Break	
<b>Session: General III Chair: Yoshiki Kawano</b>		

13:30-13:55PM	B19: Real-Time Measurement of surface stress evolution during nano-structural formation on Silicon	<b>Hidehito Asaoka</b> Japan Atomic Energy Agency, Japan
13:55-14:20PM	B20: Valence band structure of monoclinic gallium oxide studied by polarized optical measurements	<b>Takeyoshi Onuma</b> Kogakuin University, Japan
14:20-14:45PM	B21: New trends in metallic Delafossite Materials	<b>Pallavi Kushwaha</b> Max-Planck Institute For Chemical Physics of Solids, Germany
14:45-15:10PM	B22: Scaling relation of domain competition on (2+1) dimensional ballistic deposition model with surface diffusion	<b>Hiroyasu Katsuno</b> Ritsumeikan University, Japan
15:10-15:55PM	<b>Poster Session</b>	
<b>Session: General IV Chair: Takeshi Mitani</b>		
15:55-16:20PM	B23: Thin film growth of BaSi <sub>2</sub> photovoltaic material by rapid thermal evaporation	<b>Kosuke O. Hara</b> University of Yamanashi, Japan
16:20-16:35PM	B24: Morphologies of primary and eutectic silicon in hypereutectic Al-Si alloys under a low-voltage alternating current pulse	<b>Limin Zhang</b> Northwestern Polytechnical Univeristy, China
16:35-16:50PM	B25: High Magnetic Properties of Nano-sized Permanent Magnet Nd <sub>2</sub> Fe <sub>14</sub> B : Synthesis and Characterization	<b>Jihun Jung</b> Sogang University, Korea
16:50-17:05PM	B26: Bifunctional Transmission Film Composed of Phosphors and Gold Nanoparticles for Perovskite Solar Cell	<b>Taeyoung Eom</b> Sogang University, Korea
17:30PM	Dinner Social	

<b>Tuesday Dec. 15</b>		
<b>Room C</b>		
7:00-8:00AM	Breakfast	
<b>Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications I</b>		
<b>Chair: Zlatko Sitar</b>		
8:00-8:25AM	C09: Photoelectric energy conversion in GaN porous nanostructures formed by electrochemical process	<b>Taketomo Sato</b> Hokkaido University, Japan
8:25-8:50AM	C10: Solar Light Driven Selective Methanol Production via Artificial Photosynthesis Devices Fabrication	<b>YoungSoo Kang</b> Sogang University, Korea
8:50-9:15AM	C11: Dislocation Passivation by Positive Usage of Phase Separation During InGaN Growth by DERI Method	<b>Yasushi Nanishi</b> Ritsumeikan University, Japan
9:15-9:40AM	C12: Technical issues of GaInN growth with high indium composition for LEDs	<b>Tohru Honda</b> Kogakuin University, Japan
9:40-10:05AM	C13: Precise Growth Control for AlGaIn/GaN Superlattices by MBE and MOCVD for Developing GaN-Based THz Quantum Cascade Lasers	<b>Wataru Terashima</b> RIKEN Quantum Optodevice Laboratory, Japan
10:05-10:20AM	Session Break	
<b>Session: 2D atomic layered materials II Chair: Bene Poelsema</b>		
10:20 -10:45AM	C14: Nanopatterning of Graphene Films by Local Catalytic Etching Using Metal Nanoparticles	<b>Toshio Ogino</b> Yokohama National University, Japan
10:45-11:10AM	C15: Soft-mode instabilities and electronic correlations in strained 2D materials	<b>Chris A. Marianetti</b> Columbia University, USA
11:10-11:35AM	C16: Controlling the Space Distribution of Composition and Electronic Structure in Two dimensional Layered Semiconductor	<b>Xidong Duan</b> Hunan University, China
12:00-13:30PM	Lunch Break	
<b>Session: Single crystals I Chair: Jarkko Leiro</b>		
13:30-13:55PM	C17: Stability of micro and nano single crystal rods and wires	<b>Harris Wong</b> Louisiana State University, USA

13:55-14:20 PM	C18: Single-crystal film growth of organic semiconductors using inkjet printing	<b>Hiromi Minemawari</b> National Institute of Advanced Industrial Science and Technology (AIST), Japan
14:20-14:45PM	C19: Single crystal growth of Fe-Ga alloys by the Czochralski method for application to vibration energy harvesting	<b>Shun Fujieda</b> Tohoko University, Japan
14:45-15:10PM	C20: Single Crystal Growth for Functional Materials	<b>Youguo Shi</b> Institute of Physics, CAS China
15:10-15:55PM	<b>Poster Session</b>	
<b>Session: Epitaxial thin films and nanostructures V Chair: Bernd Rauschenbach</b>		
15:55-16:20PM	C21: In situ X-ray synchrotron and optical analysis of ZnO Growth by Atomic Layer Deposition	<b>Elisabeth Blanquet</b> University of Grenoble Alpes, France
16:20-16:45PM	C22: Pulsed laser deposition of epitaxial silicon carbide and aluminum nitride thin films on silicon substrates	<b>Hideki Nakazawa</b> Hirosaki University, Japan
16:45-17:10PM	C23: InGaAs and InP grown on silicon for high mobility CMOS	<b>Jiaoqing Pan</b> Institute of semiconductors, CAS, China
17:30PM	Dinner Social	



<b>Tuesday Dec. 15</b>		
<b>Room D</b>		
7:00-8:00AM	Breakfast	
<b>Session: Crystal engineering II Chair: Kader Zaidat</b>		
8:00-8:25AM	D09: Integrated Hybrid Semiconductors: Structural, Chemical, and Electrical Properties	<b>Mark Goorsky</b> University of California, Los Angeles, USA
8:25-8:50AM	D10: Influence on carrier recombination of Cu(In,Ga)Se <sub>2</sub> solar cells induced by device processing	<b>Jiro Nishinaga</b> National Institute of Advanced Industrial Science and Technology (AIST), Japan
8:50-9:15AM	D11: H-Bond Stitched Nano-Porous Molecular Framework Materials	<b>Jean-Pascal Sutter</b> CNRS, Coordination Chemistry Lab (LCC), France
9:15-9:40AM	D12: Experimental and numerical aspects of the Kyropoulos Crystal Growth of Silicon for Photovoltaics	<b>Guy Chichignoud</b> SIMAP EPM CNRS, France
9:40-10:05AM	D13: Characterization of the dendrite structure during solidification: A study using synchrotron X-ray tomography and 3-D phase field modeling approaches	<b>Zhipeng Guo</b> Tsinghua University, China
10:05-10:20AM	Session Break	
<b>Session: Single crystals II Chair: Harris Wong</b>		
10:20-10:45AM	D14: Crystal Growth and piezoelectric properties of Ca <sub>3</sub> Ta(Ga <sub>1-x</sub> Al <sub>x</sub> ) <sub>3</sub> Si <sub>2</sub> O <sub>14</sub> single crystals	<b>Tetsuo Kudo</b> Tohoku University, Japan
10:45-11:10AM	D15: Cleavage properties of muscovite mica and PbS single crystals	<b>Jarkko Leiro</b> University of Turku, Finland
11:10-11:35AM	D16: Comparisons between 5 at% Yb-doped LuPO <sub>4</sub> and Yb-doped Lu <sub>0.5</sub> Y <sub>0.5</sub> PO <sub>4</sub> crystals on absorption spectra	<b>Bing Teng</b> Qingdao University, China
12:00-13:30PM	Lunch Break	
<b>Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications II Chair: YoungSoo Kang</b>		
13:30-13:55PM	D17: Growth of Thick InGaN and GaN by Tri-Halide Vapor Phase Epitaxy with high rate	<b>Hisashi Murakami</b> Tokyo University of Agriculture & Technology, Japan

13:55-14:20PM	D18: Surface kinetics and surface morphology in MOCVD growth on III-nitride substrates	<b>Zlatko Sitar</b> North Carolina State University, USA
14:20 -14:45 PM	D19: Chemical vapor deposition of aluminium nitride from halide precursors for thin films and coatings	<b>Michel Pons</b> University of Grenoble Alpes, France
14:45-15:10PM	D20: High speed growth of InN by HVPE realized by controlled generation of InCl <sub>3</sub>	<b>Rie Togashi</b> Tokyo University of Agriculture and Technology, Japan
15:10-15:55PM	<b>Poster Session</b>	
<b>Session: Crystal engineering III Chair: Mark Goorsky</b>		
15:55-16:20PM	D21: Phase Transformations and Structure-Property Relationships in Ceramics	<b>Cristian V. Ciobanu</b> Colorado School of Mines, USA
16:20-16:45PM	D22: Phase Transformation of Calcium-based Minerals to Remove Fluoride from Aqueous Solutions	<b>Il Won Kim</b> Soongsil University, Korea
16:45-17:00PM	D23: Materials crystallization at mesoscale	<b>Dongfeng Xue</b> Changchun Institute of Applied Chemistry, CAS, China
17:30PM	Dinner Social	

<b>Wednesday Dec. 16</b>		
<b>Room B</b>		
7:00-8:00AM	Breakfast	
<b>Session: Radiation Detector Materials - From Crystal Growth to Device Applications II</b>		
<b>Chair: HongJoo Kim</b>		
8:00-8:25AM	B27: Facile fabrication of porphyrin Janus particles from water droplet template at oil-aqueous interface	<b>Jingxia Wang</b> Technical Institute of Physics and Chemistry, China
8:25-8:50AM	B28: GaSb alternative substrates for MBE growth of next generation HgCdTe infrared detectors	<b>Wen Lei</b> University of Western Australia, Australia
<b>Session: III-Nitrides for Lighting, Photovoltaics and Sensing Applications III</b>		
<b>Chair: Yasushi Nanishi</b>		
8:50-9:15AM	B29: Preparation of III-Nitride Devices for Large Area Light Emitting Devices and Solar Cells	<b>Hiroshi Fujioka</b> The University of Tokyo, Japan
9:15-9:40AM	B30: Recent Advances in Basic Ammonothermal Growth of Gallium Nitride	<b>Siddha Pimputkar</b> University of California, USA
9:40-10:05AM	B31: InGaN pyramidal quantum dot as a source of single photons	<b>Houssaine Machhadani</b> Linköping University, Sweden
10:05-10:20AM	Session Break	
<b>Session: Crystal engineering IV Chair: Zhipeng Guo</b>		
10:20-10:45AM	B32: Layer crystal growth with fractal analysis technique: from theory to engineering application	<b>Xiaobin Jiang</b> Dalian University of Technology, China
10:45-11:10AM	B33: Engineering Functional Materials by Halogen Bonding	<b>Giancarlo Terraneo</b> Politecnico di Milano, Italy
11:10-11:35AM	B34: Crystal growth control in chalcogenide and its application to multilevel storage in phase-change memory	<b>You Yin</b> Gunma University, Japan
12:00-13:30 PM	Lunch Break	
<b>Session: Epitaxial thin films and nanostructures VI Chair: Sylke Blumstengel</b>		
13:30-13:55PM	B35: Monolithic integrated Ge light emitters fabricated by epitaxial lateral overgrowth	<b>Katsuya Oda</b> Hitachi Ltd., Research & Development Group, Japan

13:55-14:20PM	B36: Atomically Engineered Metal-Insulator Transition at the TiO <sub>2</sub> /LaAlO <sub>3</sub> Heterointerface	<b>Makoto Minohara</b> High Energy Accelerator Research Organization (KEK), Japan
14:20 -14:45 PM	B37: Thermodynamics and kinetics of nanocluster formation on semiconductor surfaces	<b>Andreas Fissel</b> Leibniz University Hannover, Germany
14:45-15:10PM	B38: Epitaxial growth of metastable oxide thin films under atmosphere	<b>Kentaro Kaneko</b> Kyoto University, Japan
15:10-15:25PM	Session Break	
<b>Session: Epitaxial thin films and nanostructures VII Chair: Hans Von Känel</b>		
15:25-15:45PM	B39: Growth and Characterization of Full Flux-closure Quadrants in PbTiO <sub>3</sub> thin films	<b>Yinlian Zhu</b> Institute of Metal Research, CAS, China
15:45-16:10PM	B40: Synthesis of Polar and Non-Polar Epitaxial GaN Thin Films by Ion-Beam Nitridation of Ga Droplets	<b>Jürgen W. Gerlach</b> Leibniz Institute of Surface Modification (IOM), Germany
16:10-16:35PM	B41: Epitaxial growth of hybrid inorganic/organic semiconductor structures	<b>Sylke Blumstengel</b> Humboldt-Universität zu Berlin, Germany
16:35-17:00PM	B42: Epitaxially stabilized oxide film composed of twisted triangular-lattice layers	<b>Masaki Uchida</b> The University of Tokyo, Japan
17:00-17:25PM	B43: Growth temperature dependence of crystalline state of low-temperature-grown InGaAs on InP substrate	<b>Yoriko Tominaga</b> Hiroshima University, Japan
17:30PM	Dinner Social	

<b>Wednesday Dec. 16</b>		
<b>Room C</b>		
7:00-8:00AM	Breakfast	
<b>Session: General V Chair: Jean-Noel Aqua</b>		
8:00-8:25AM	C24: Supercooled liquids, glasses and growth of dendrites under out of equilibrium conditions	<b>Francesco Aliotta</b> Istituto per I Processi Chimici-Fisici, CNR Italy
8:25-8:50AM	C25: Electric Field Assisted Growth of Organic Conductive wire and Self-aligned Organic Nanotransistor	<b>Masatoshi Sakai</b> Chiba University, Japan
8:50-9:15AM	C26: Calcium minerals crystal growth for dental material applications	<b>Yuki Sugiura</b> Kyushu University, Japan
9:15-9:40AM	C27: Morphology effect on the nano-hematite and its magnetic property	<b>Yen-Hua Chen</b> National Cheng Kung University, Taiwan
9:40-10:05AM	C28: Dynamics of Multi-functional Materials with Inelastic Neutron Scatterings	<b>Dehong Yu</b> Australian Nuclear Science and Technology Organisation, Australia
10:05-10:20AM	Session Break	
<b>Session: General VI Chair: Alexander Gelfgat</b>		
10:20-10:45AM	C29: Structural diversity of multi-component self-assembled systems	<b>Irene Ling</b> University of Malaya, Malaysia
10:45-11:10AM	C30: Magnetocaloric effect in multifunctional perovskites	<b>Suja Elizabeth</b> Indian Institute of Science, India
11:10-11:35AM	C31: Strain-engineered SiGe nanomembranes on Porous Silicon stressor	<b>Jean-Noel Aqua</b> Universit éParis 6 – INSP, France
11:35-12:00PM	C32: Silicon Nanostructures for Nanoelectronics and Photovoltaics	<b>Noushine Shahidzadeh</b> University of Amsterdam, The Netherlands
12:00-13:30 PM	Lunch Break	
<b>Session: Crystal engineering V Chair: Guy Chichignoud</b>		

13:55-14:20PM	C33: Morphology Control of Metal Oxide Crystals for Multifunctional Cosmetic Application	<b>Tsugio Sato</b> Tohoku University, Japan
14:20-14:45PM	C34: Crystal engineering of cocrystals: air-stable cyclohexasulfur as cocrystal	<b>Kunihisa Sugimoto</b> Japan Synchrotron Radiation Research Institute (JASRI), Japan
14:45 -15:10PM	C35: Drug beneficiation via cyclodextrin inclusion	<b>Mino R. Caira</b> University of Cape Town, South Africa
15:10-15:25PM	Session Break	
<b>Session: Crystal engineering VI Chair: Kader Zaidat</b>		
15:25 -15:50PM	C36: The discrete crystal growth: multi-scale phenomena, mechanism and influence on segregation	<b>Xiaoping Ma</b> Institute of Metal Research, CAS, China
15:50-16:15PM	C37: In Situ Study of the Crystal Formation Process of Molecular Materials	<b>Yang Liu</b> Shandong University, China
16:15-16:40PM	C38: Wetting and joining of structural materials by growth of metal borates nano/micro whiskers	<b>Jian Cao</b> Harbin Institute of Technology, China
17:30PM	Dinner Social	

<b>Wednesday Dec. 16</b>		
<b>Room D</b>		
7:00-8:00AM	Breakfast	
<b>Session: Epitaxial thin films and nanostructures VIII Chair: Kosuke Matsuzaki</b>		
8:00-8:25AM	D24: Growth of strained Si/SiGe on Si(110) substrates for realization of high-mobility devices	<b>Keisuke Arimoto</b> University of Yamanashi, Japan
8:25-8:50AM	D25: Construction of well-defined 3D transition metal oxides nanostructures and their novel properties	<b>Azusa N. Hattori</b> Osaka University, Japan
8:50-9:15AM	D26: A-site driven ferroelectricity in strained La <sub>2</sub> NiMnO <sub>6</sub> thin films	<b>Ryota Takahashi</b> University of Tokyo, Japan
9:15-9:40AM	D27: Synthesis of Heteroatom-Containing Nanocarbon Materials by Solution Plasma Process in Organic Solution	<b>Takahiro Ishizaki</b> Shibaura Institute of Technology, Japan
9:40-10:05AM	D28: Modified InAs/GaAs quantum dots for enhanced solar cell efficiency	<b>Jose Mar <sup>á</sup> Ulloa</b> Universidad Polit <sup>é</sup> cnica de Madrid, Spain
10:05-10:20AM	Session Break	
<b>Session: Epitaxial thin films and nanostructures IX Chair: Masaki Uchida</b>		
10:20-10:45AM	D29: Low Temperature Deposition of Epitaxial (K,Na)NbO <sub>3</sub> Films using Hydrothermal Method	<b>Takahisa Shiraishi</b> Tohoku University, Japan
10:45-11:10AM	D30: Epitaxial Growth of InAs-based Quantum Structures on GaAs	<b>Itaru Kamiya</b> Toyota Technological Institute, Japan
11:10-11:35AM	D31: Epitaxial growth of bipolar conducting Cu <sub>3</sub> N (100) thin films	<b>Kosuke Matsuzaki</b> Tokyo Institute of Technology, Japan
11:35-12:00PM	D32: A-axis Growth of nano structured VO <sub>2</sub> Thin films by Pulsed Laser Deposition on substrate glass	<b>Balla Diop Ngom</b> Universit Cheikh Anta Diop de Dakar (UCAD), Senegal
12:00-13:30PM	Lunch Break	
<b>Session: General VII Chair: Masaharu Oshima</b>		
13:55-14:20PM	D33: Non-intrusive instability measurements in a model of Czochralski melt flow	<b>Alexander Gelfgat</b> Tel Aviv University, Israel

14:20 -14:45 PM	D34: Thermal conductive graphene quantum dots for the electromagnetic interference	<b>Hyonkwang Choi</b> Inje University, Korea
14:45 -15:10 PM	D35: Multiple pathway of nucleation from levitated solution droplets	<b>Geun Woo Lee</b> Korea Research Institute of Standards and Science, Korea
15:10-15:25PM	Session Break	
<b>Session: General VIII Chair: Francesco Aliotta</b>		
15:25-15:50PM	D36: Solution growth of 4H-SiC crystals with Si and Si based alloy solvents	<b>Takeshi Mitani</b> National Institute of Advanced Industrial Science and Technology, Japan
15:50-16:15PM	D37: Operando spectronanoscropy for graphene FET and ultrathin organic film FET	<b>Masaharu Oshima</b> The University of Tokyo, Japan
16:15-16:40PM	D38: Metastability Limit for the Nucleation of NaCl Crystals in Confinement	<b>Daniel Bonn</b> University of Amsterdam, The Netherlands
17:30PM	Dinner Social	



**Tuesday Dec. 15**

15:10-15:55PM

**Poster Session**

P01	Electrical and optical properties of ZnO films prepared by solution film forming method	<b>Saki Fukui</b> Tohoku University Japan
P02	Inkjet Printing Patterned Photonic Crystal Domes for Wide Viewing-angle by the Sliding Three Phase Contact Line	<b>Minxuan Kuang</b> Institute of Chemistry, CAS China
P03	Morphological Controlled Synthesis of ZnO for the application to sunscreen cosmetic	<b>Mizuki Yoshida</b> Tohoku University Japan
P04	Synthesis and NIR-Shielding Ability of Nb-doped TiO <sub>2</sub> by Solvothermal Approach	<b>Makoto Hsmanaka</b> Tohoku University Japan
P05	Single crystal growth of SiC using high temperature chemical vapor deposition from methyltrichlorosilane	<b>Seongmin Jeong</b> Korea Institute of Ceramic Engineering and Technology (KICET) Korea
P06	Crystal Growth and Superconductivity of half-Heusler Compounds ErPdBi and HoPdBi	<b>Yingkai Huang</b> University of Amsterdam The Netherlands
P07	Solvothermal synthesis of ternary ZnSSe nanorods with tunable band gap and its photoluminescence enhancement	<b>Lin-Jer Chen</b> National Cheng Kung University Taiwan